AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1-7. (Cancelled)

8. (Currently amended) A solid-state imaging apparatus comprising:

a substrate;

a first pixel formed on the substrate including a first photodiode, a first transfer transistor and a first floating diffusion;

a second pixel formed on the substrate adjacent to the first pixel including a second photodiode, a second transfer transistor and a second floating diffusion;

a reset transistor formed on the substrate; and

an amplifier transistor formed on the substrate,

wherein a gate electrode of the amplifier transistor is connected to the first floating diffusion and the second floating diffusion,

a source of the reset transistor is connected to the first floating diffusion and the source of the reset transistor is connected to the second floating diffusion, and

a distance ~~and direction from~~ between the first photodiode [[to]] and the first floating diffusion [[are]] is substantially equal to a distance ~~and direction from~~ between the second photodiode [[to]] and the second floating diffusion, and

a vertical direction position and a horizontal direction position of the first floating diffusion when viewed from the first photodiode are substantially the same as a vertical direction position and a horizontal direction position of the second floating diffusion when viewed from the second photodiode.

9. (Previously presented) The solid-state imaging apparatus of claim 8, further comprising:

a power supply interconnect; and

an output interconnect,

wherein the power supply interconnect is connected to a drain of the reset transistor and a source of the amplifier transistor, and

the output interconnect is connected to a drain of the amplifier transistor.

10. (Previously presented) The solid-state imaging apparatus of claim 8,

wherein the amplifier transistor is formed in the first pixel,

the reset transistor is formed in the second pixel, and

a distance and direction from the first photodiode to the amplifier transistor are substantially equal to a distance and direction from the second photodiode to the reset transistor.

11. (Previously presented) The solid-state imaging apparatus of claim 8, wherein a shape and size of the first pixel are substantially equal to a shape and size as that of the second pixel.

12. (Previously presented) The solid-state imaging apparatus of claim 8, wherein the solid-state imaging apparatus comprises a plurality of units, and

each of the units includes only the first pixel, the second pixel, the reset transistor and the amplifier transistor.

13. (Previously presented) The solid-state imaging apparatus of claim 8, wherein the amplifier transistor and the reset transistor are formed in the second pixel and a drain of the reset transistor is a source of the amplifier transistor.

14. (Previously presented) The solid-state imaging apparatus of claim 8, further comprising:

a row-select unit formed on the substrate, and

a column-select unit formed on the substrate,

wherein gates of the first transfer transistor and the second transfer transistor are connected to the row select unit, and

a drain of the amplifier transistor is connected to the column-select unit.